L Number	Hits	Search Text	DB	Time stamp
-	18	((integrated near3 circuit near3 design) or (IC near3 design) or (semiconductor near3 device)) and module and (wir$3 near3 layer) and ((horizontal and vertical and diagonal) near3 direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 14:37
-	1	((integrated near3 circuit near3 design) or (IC near3 design) or (semiconductor near3 device)) and module and (wir$3 near3 layer near3 (multipl$3 or plural$3)) and ((horizontal and vertical and diagonal) near3 direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 16:01
-	1	((integrated near3 circuit near3 design) or (IC near3 design) or (semiconductor near3 device)) and module and (wir$3 near3 layer near3 (multipl$3 or plural$3 or multilayer or (mult$3 near3 layer))) and ((horizontal and vertical and diagonal) near3 direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 16:06
-	15	((integrated near3 circuit near3 design) or (IC near3 design) or (semiconductor near3 device)) and module and ((mult$3 or plural$3) near3 layer) and ((horizontal and vertical and diagonal) near3 direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 16:31
-	17	((integrated near3 circuit) or IC or semiconductor) and module and ((mult$3 or plural$3) near3 layer) and ((horizontal and vertical and diagonal) near3 direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 16:39
-	1236	((integrated near3 circuit) or IC or semiconductor) and module and ((mult$3 or plural$3) near3 layer) and ((five or fifth) near3 layer) ((horizontal and vertical and diagonal) near3 direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 16:42
-	366	((integrated near3 circuit) or IC or semiconductor) and module and ((mult$3 or plural$3) near3 layer) and ((five or fifth) near3 layer) ((horizontal and vertical and diagonal) near3 direction) and (gridless near3 non near3 manhattan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 16:44
-	2	((integrated near3 circuit) or IC or semiconductor) and module and ((mult$3 or plural$3) near3 layer) and ((five or fifth) near3 layer near3 metal near3 wir$3) ((horizontal and vertical and diagonal) near3 direction) and (gridless near3 non near3 manhattan) and orthogonal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 16:49
-	366	((integrated near3 circuit) or IC or semiconductor) and module and ((mult$3 or plural$3) near3 layer) and ((five or fifth) near3 layer) ((horizontal and vertical and diagonal) near3 direction) and (gridless near3 non near3 manhattan) and orthogonal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 08:23
-	0	((integrated near3 circuit) or IC or semiconductor) and module and ((mult$3 or plural$3) near3 layer) and ((five or fifth) near3 layer) and ((horizontal and vertical and diagonal) near3 direction) and (gridless near3 non near3 manhattan) and orthogonal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 08:24
-	15	((integrated near3 circuit) or IC or semiconductor) and module and ((mult$3 or plural$3) near3 layer) and ((five or fifth) near3 layer) and ((horizontal and vertical and diagonal) near3 direction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 08:52
-	148	((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 10:10
-	2	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and gridless	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/06 15:42

-		19	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/06 15:43
-		19	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 17:11
-		2	(manhattan same gridded) and layers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 07:44
-		74	(manhattan and grid$4) and (metal near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 07:45
-		51	(manhattan and grid$4) and (metal near3 layer) and (first near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 07:46
-		36	(manhattan and grid$4) and (metal near3 layer) and (first near3 layer) and (fourth near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 09:21
-		13	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and ((manhattan and grid$4) and (metal near3 layer) and (first near3 layer) and (fourth near3 layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 09:29
-		7	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and ((manhattan and grid$4) and (metal near3 layer) and (first near3 layer) and (fourth near3 layer)) and pitch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 09:06
-		9	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and pitch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 09:15
-		15	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and (manhattan or grid$4) and (metal near3 layer) and (first near3 layer) and (fourth near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 09:23
-		9	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and pitch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 11:34
-		0	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and ((first near3 layer) near3 horizint$3) and ((second near3 layer) near3 vertic$3) and ((third near3 layer) near3 diagon$3) and ((fourth near3 layer) near3 diagon$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 11:45
-		0	((first near3 layer) near3 horizint$3) and ((second near3 layer) near3 vertic$3) and ((third near3 layer) near3 diagon$3) and ((fourth near3 layer) near3 diagon$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 11:38

-	0	((first near3 layer) near3 horizont$3) and ((second near3 layer) near3 vertic$3) and ((third near3 layer) near3 diagon$3) and ((fourth near3 layer) near3 diagon$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 11:38
-	16	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and (horizontal and vertical and diagonal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 17:04
-	8	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and (layer near3 (horizontal and vertical and diagonal))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 12:12
-	11	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and (horizontal and vertical and diagonal) and @pd<=20030115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 16:59
-	11	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and (horizontal and vertical and diagonal) and @pd<=20030115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 17:04
-	11	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and (horizontal and vertical and diagonal) and @pd<=20030115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/18 17:05
-	14	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and @pd<=20030115	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/22 09:32
-	0	simulated adj1 euclidean adj1 wiring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/21 15:30
-	0	simulated near2 euclidean near2 wiring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/21 15:30
-	0	euclidean near3 wir$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/21 16:22
-	0	euclidean near3 wiring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/21 16:42
-	0	(euclidean near3 (wiring or wir$3 or distance)) same (integrated near3 circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/21 16:43
-	1	"6324674".PN.	USPAT; US-PGPUB	2003/04/21 16:49
-	0	"2001/0009031".PN.	USPAT; US-PGPUB	2003/04/21 16:56
-	0	"2001/0009031".PN.	USPAT; US-PGPUB	2003/04/21 16:55
-	0	"2001/0009031".PN.	USPAT; US-PGPUB	2003/04/21 16:55

-		0	"2001/0009031".PN.	USPAT; US-PGPUB	2003/04/21 16:55
-		0	"2001/0009031".PN.	USPAT; US-PGPUB	2003/04/21 16:55
-		1	"6412097".PN.	USPAT; US-PGPUB	2003/04/21 16:55
-		0	"2001/0009031".PN.	USPAT; US-PGPUB	2003/04/21 16:55
-		1	20010009031.pn.	USPAT; US-PGPUB	2003/04/21 16:56
-		1	"6412097".PN.	USPAT; US-PGPUB	2003/04/21 17:00
-		0	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and manhattan and layers and (ratio same ((first and second) near3 line))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/22 09:35
-		0	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and layers and (ratio same ((first and second) near3 line))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/22 09:35
-		17	(((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) and layers and (ratio same length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 12:18
-		23	((((non near3 manhattan) or nonmanhattan or diagonal) near3 wiring) same ratio) and layers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/22 14:18
-		27	(((non adj manhattan) or nonmanhattan or diagonal) near3 (wiring or direction)) and layers and (ratio same length) and (((horizontal and vertical) or orthogonal) near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 12:20
-		27	(((non adj manhattan) or nonmanhattan or diagonal) near3 (wiring or direction)) and layers and (ratio same length) and (((horizontal and vertical) or orthogonal or manhattan) near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/30 17:46
-		15	(((non adj manhattan) or nonmanhattan or diagonal) near3 (wiring or direction)) and layers and (ratio same length) and (((horizontal and vertical) or orthogonal or manhattan) near3 layer) and ((sixty adj degrees) or (US-20020147958-A1.DID. adj degrees))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 13:52
-		0	(((non adj manhattan) or nonmanhattan or diagonal) near3 (wiring or direction)) and layers and (ratio same length) and (((horizontal and vertical) or orthogonal or manhattan) near3 layer) and ((sixty adj degrees) or (US-20020147958-A1.DID. adj degrees)) and ((fourty adj five adj degrees) or (US-5801422-A.DID. adj degrees))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 13:56
-		0	(((non adj manhattan) or nonmanhattan or diagonal) near3 (wiring or direction)) same layer and (ratio same length) and (((horizontal and vertical) or orthogonal or manhattan) near3 layer) and ((sixty adj degrees) or (US-20020147958-A1.DID. adj degrees)) and ((fourty adj five adj degrees) or (US-5801422-A.DID. adj degrees))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 13:57
-		11	(((non adj manhattan) or nonmanhattan or diagonal) near3 (wiring or direction)) same layer and (ratio same length) and (((horizontal and vertical) or orthogonal or manhattan) near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 13:57
-		0	Ecker.in.	IBM_TDB	2004/01/30 15:16
-		6	semiconductor adj package adj structure	IBM_TDB	2004/01/30 15:20
-		1	diagonal adj rectangular adj wiring	IBM_TDB	2004/01/30 15:20

-	91	((non adj manhattan) or nonmanhattan or diagonal) same (wiring or direction) same layers and (ratio same length) and ((horizontal and vertical) or orthogonal or manhattan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/30 17:49
-	1	((non adj manhattan) or nonmanhattan or diagonal) same (wiring or direction) same layers and (ratio same length) and ((horizontal and vertical) or orthogonal or manhattan) and 716/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/30 17:49